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Effect of oxygen on dislocation multiplication in silicon crystals

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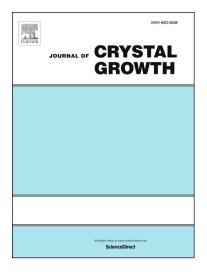
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Wataru Fukushima^a, Hirofumi Harada^b, Yoshiji Miyamura^b, Masato Imai^c, Satoshi Nakano^b, Koichi Kakimoto^{a,b}

^aDepartment of Aeronautics and Astronautics, Kyushu University, 744 Motooka,

Nishi-ku, Fukuoka 819-0395, Japan

^bResearch Institute for Applied Mechanics, Kyushu University, 6-1 Kasuga-koen,

Kasuga, Fukuoka 816-8580, Japan

^cFaculty of Engineering, University of Miyazaki,

Gakuen-kibanadai-nishi-1-1, Miyazaki, 889-212, Japan

e-mail:kakimoto@riam.kyushu-u.ac.jp

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